

Fast switching diode chip in Emitter Controlled 3 -Technology

#### Features:

- 600V Emitter Controlled 3 technology 70 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

## This chip is used for:

- Power module
- Discrete components



#### **Applications:**

- Drives
- White goods
- Resonant applications

Chip Type	<b>V</b> <sub>R</sub>	<b>I</b> F	Die Size	Package
SIDC02D60C8	600V	6A	1.4 x 1.65 mm <sup>2</sup>	sawn on foil

## **Mechanical Parameters**

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Raster size	1.4 x 1.65		
Area total	2.31	mm <sup>2</sup>	
Anode pad size	0.97 x 1.22		
Thickness	70	μm	
Wafer size	200	mm	
Max. possible chips per wafer			
Passivation frontside	Photoimide		
Pad metal	3200 nm AlSiCu		
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding		
Die bond	Electrically conductive glue or solder		
Wire bond	re bond AI, ≤500µm		
Reject ink dot size	Ø 0.65mm; max 1.2mm		
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23℃		

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### **Maximum Ratings**

Parameter	Symbol	Condition	Value	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	<i>T</i> <sub>vj</sub> = 25 ℃	600	V	
Continuous forward current	I <sub>F</sub>	<i>T</i> <sub>vj</sub> < 150℃	1)	A	
Maximum repetitive forward current	I <sub>FRM</sub>	<i>T</i> <sub>vj</sub> < 150℃	12		
Junction temperature range	$T_{vj}$		-40+175	°C	
Operating junction temperature	$T_{\rm vj}$		-40+150	°C	
Dynamic ruggedness <sup>2)</sup>	$P_{max}$	$I_{\text{Fmax}} = 12\text{A}, \ V_{\text{Rmax}} = 600\text{V}, \ T_{\text{vj}} \le 150^{\circ}\text{C}$	tbd	kW	

<sup>1)</sup> depending on thermal properties of assembly

## Static Characteristics (tested on wafer), $T_{vj} = 25 \text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	Oilit
Reverse leakage current	$I_{R}$	V <sub>R</sub> =600V			27	μA
Cathode-Anode breakdown Voltage	$V_{\rm BR}$	I <sub>R</sub> =0.25mA	600			V
Diode forward voltage	$V_{F}$	I <sub>F</sub> =6A	1.25	1.6	1.95	V

#### **Further Electrical Characteristics**

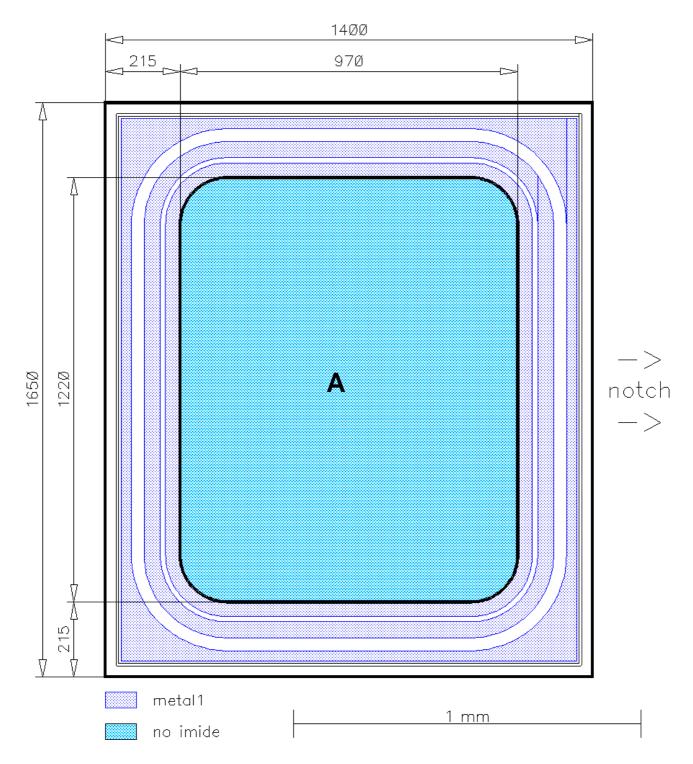
Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

<sup>&</sup>lt;sup>2)</sup> not subject to production test - verified by design/characterisation



## **Chip Drawing**

Die-Size 1400 um x 1650 um



## A: Anode pad

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Description
AQL 0,65 for visual inspection according to failure catalogue
Electrostatic Discharge Sensitive Device according to MIL-STD 883

### **Revision History**

Version	Subjects (major changes since last revision)	Date

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